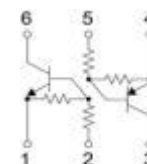
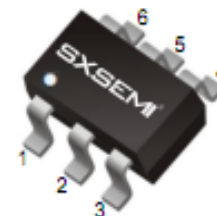


SOT-363



Marking: D10

FEATURES

- Both the DTC123J chip and DTA123J chip in a package
- Mounting possible with SOT-363 automatic mounting machines
- Transistor elements are independent, eliminating interference
- Mounting cost and area be cut in half

T_{R1} Absolute maximum ratings (T_a=25°C)

Parameter	Symbol	Value	Unit
Supply voltage	V _{CC}	50	V
Input voltage	V _{IN}	-5~12	V
Output current	I _O	100	mA
	I _{C(MAX)}	100	
Power dissipation	P _d	150	mW
Operation Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

T_{R1} Electrical characteristics (T_a=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	V _{I(off)}	0.5			V	V _{CC} =5V, I _O =100μA
	V _{I(on)}			1.1		V _O =0.3V, I _O =5mA
Output voltage	V _{O(on)}		0.1	0.3	V	I _O /I _I =5mA/0.25mA
Input current	I _I			3.6	mA	V _I =5V
Output current	I _{O(off)}			0.5	μA	V _{CC} =50V, V _I =0
DC current gain	G _I	80				V _O =5V, I _O =10mA
Input resistance	R _I	1.54	2.2	2.86	KΩ	-
Resistance ratio	R ₂ /R ₁	17	21	26		-
Transition frequency	f _T		250		MHz	V _{CE} =10V, I _E =5mA, f=100MHz

T_{R2} Absolute maximum ratings (Ta=25°C)

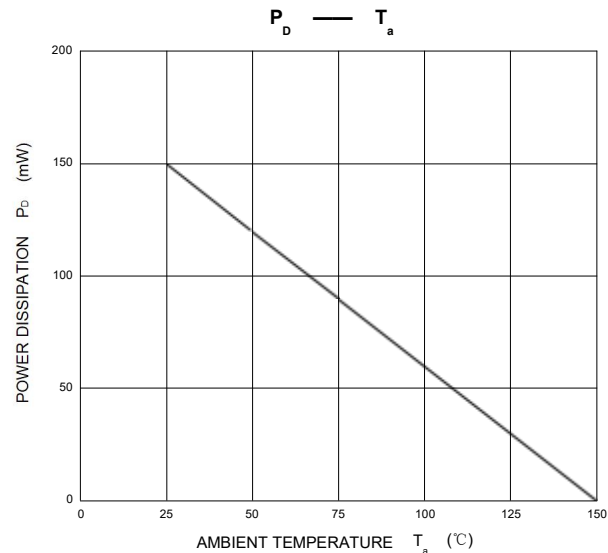
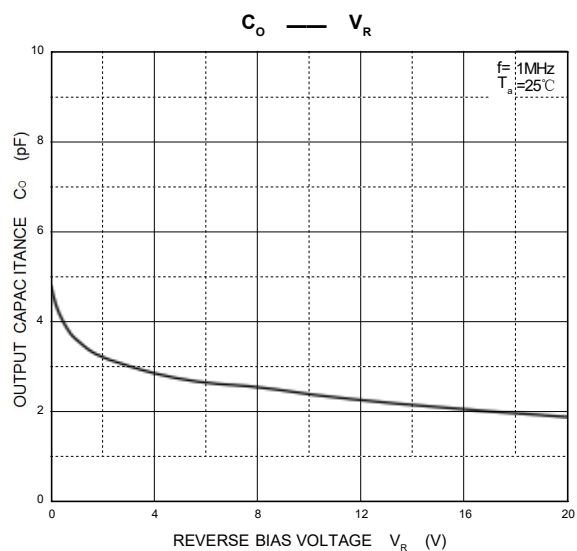
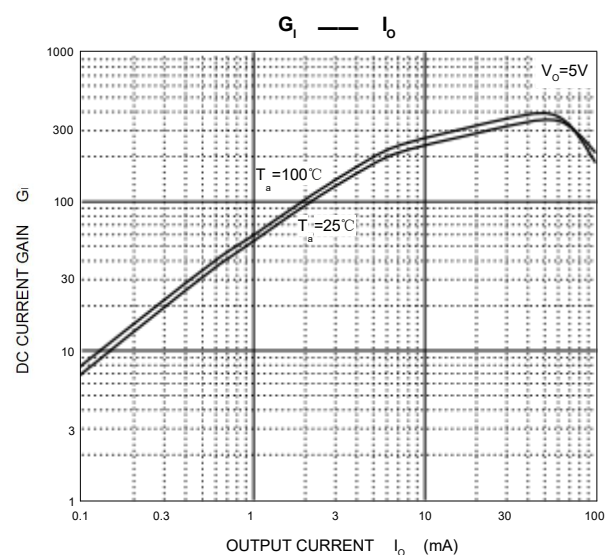
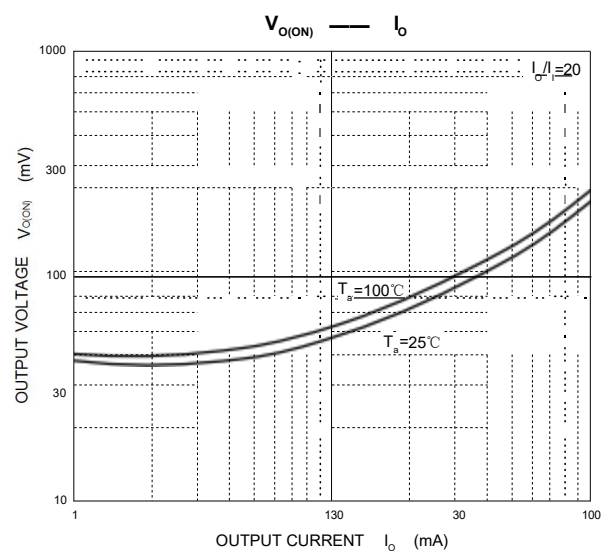
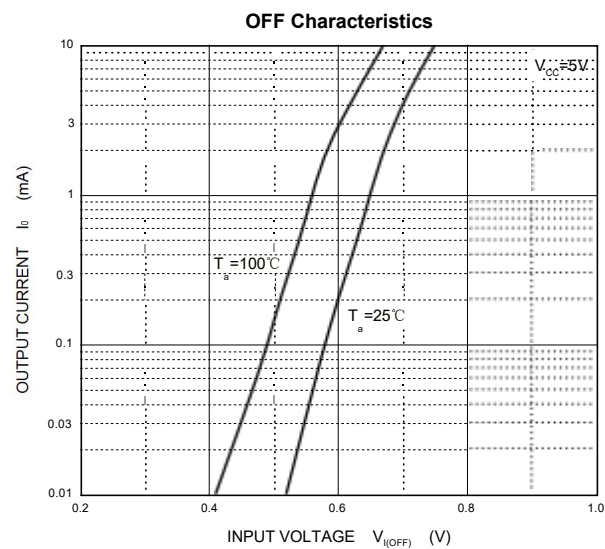
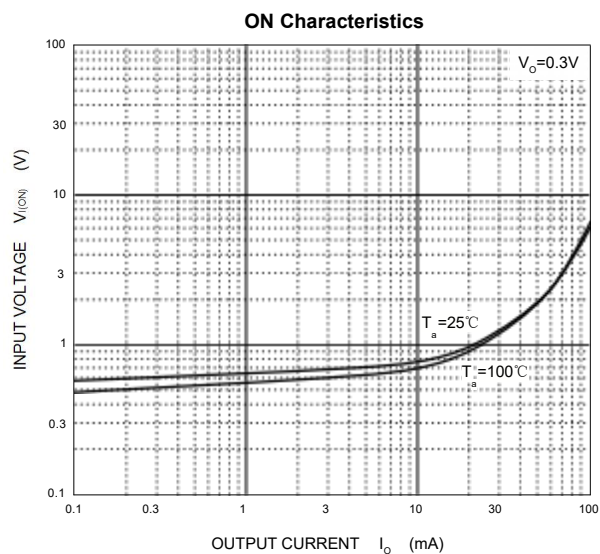
Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _{IN}	-12~5	V
Output current	I _O	-100	mA
	I _{C(MAX)}	-100	
Power dissipation	P _d	150	mW
Operation Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150	°C

T_{R2} Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	V _{I(off)}	-0.5			V	V _{CC} =-5V, I _O =-100μA
	V _{I(on)}			-1.1		V _O =-0.3V, I _O =-5mA
Output voltage	V _{O(on)}		-0.1	-0.3	V	I _O /I _I =-5mA/-0.25mA
Input current	I _I			-3.6	mA	V _I =-5V
Output current	I _{O(off)}			-0.5	μA	V _{CC} =-50V, V _I =0
DC current gain	G _I	80				V _O =-5V, I _O =-10mA
Input resistance	R ₁	1.54	2.2	2.86	KΩ	-
Resistance ratio	R ₂ /R ₁	17	21	26		-
Transition frequency	f _T		250		MHz	V _{CE} =-10V, I _E =-5mA, f=100MHz

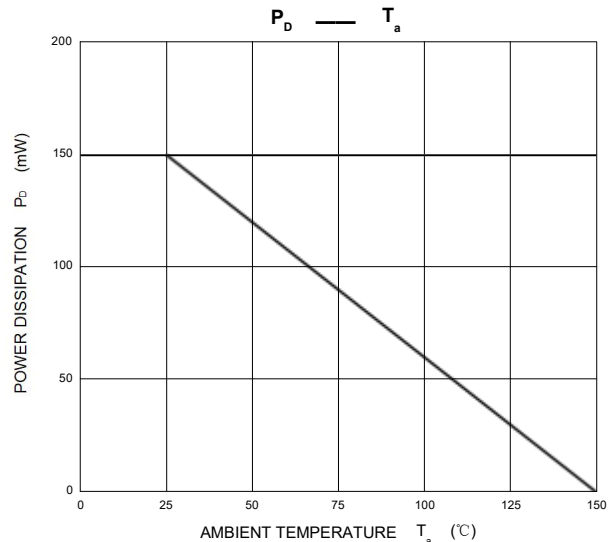
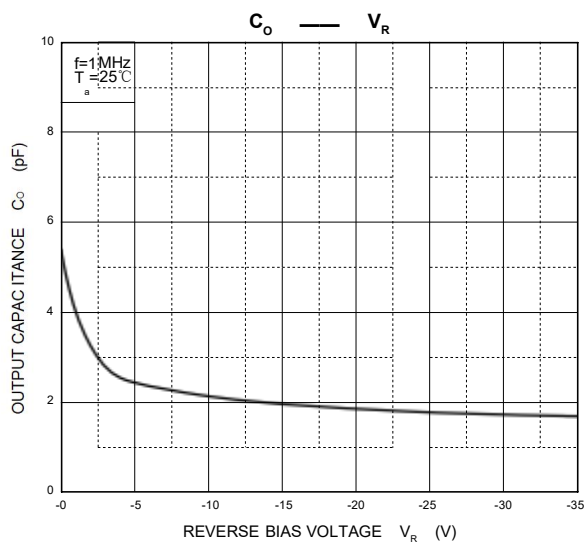
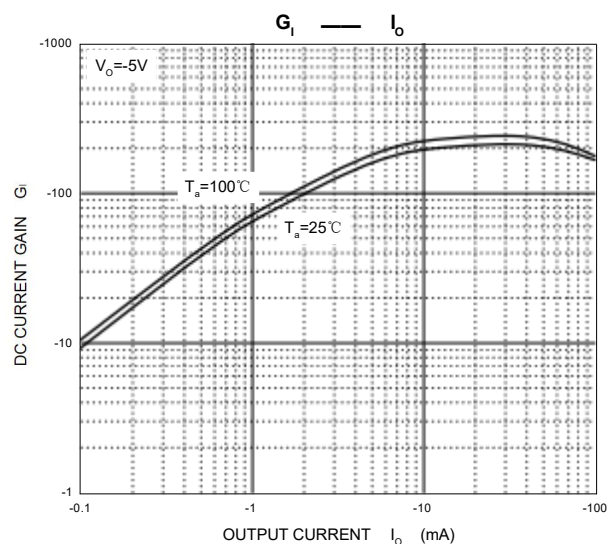
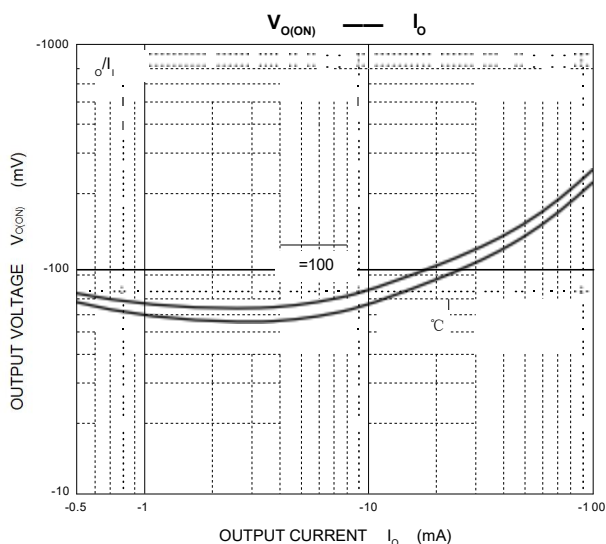
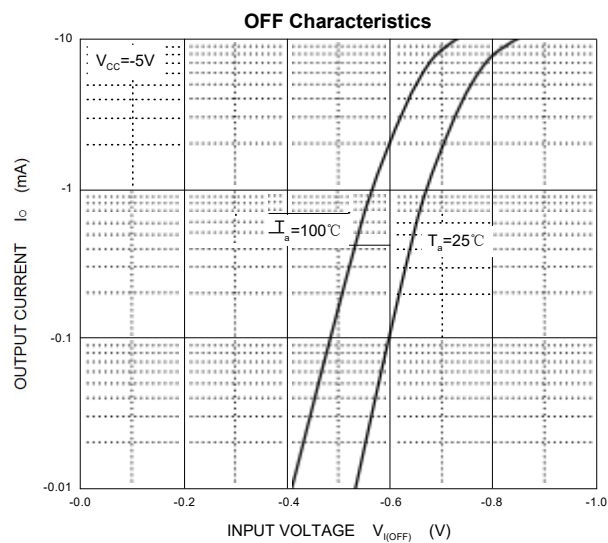
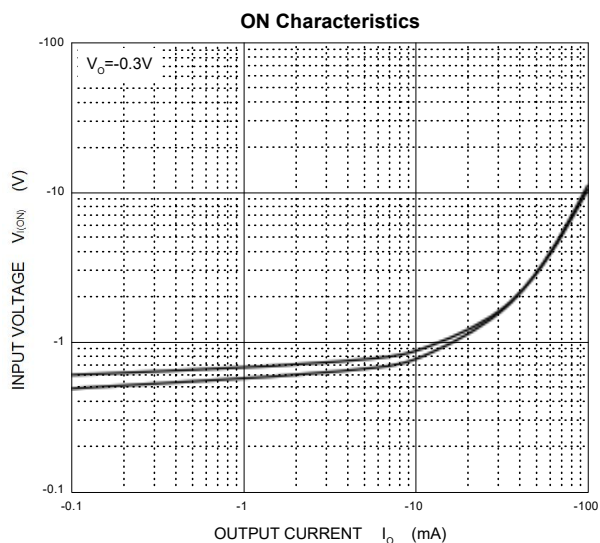
Typical Characteristics

UMD10N(NPN)

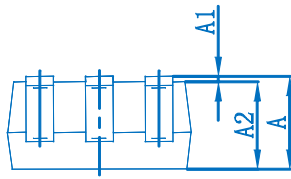
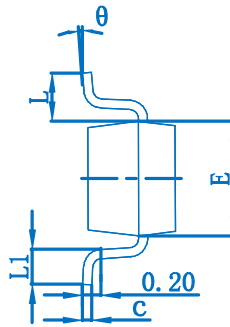
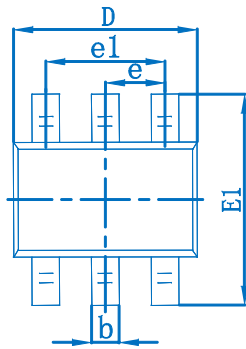


Typical Characteristics

UMD10N(PNP)

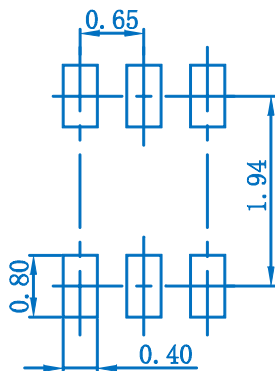


SOT-363 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.